TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HCT646AP

#### Octal Bus Transceiver/Register (3-state)

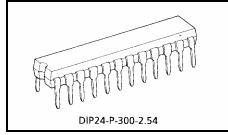
The TC74HCT646A is high speed CMOS OCTAL BUS TRANSCEIVER/REGISTERs fabricated with silicon gate  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its inputs are compatible with TTL, NMOS, and CMOS output voltage levels.

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.



Weight: 1.50 g (typ.)

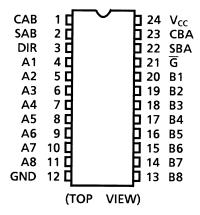
#### Features (Note 1)(Note 2)

- High speed:  $f_{max} = 60 \text{ MHz}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max)}$  at  $T_{a} = 25 \text{°C}$
- Compatible with TTL output:  $V_{IH} = 2.0 \text{ V (min)}$   $V_{IL} = 0.8 \text{ V (max)}$
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance: | I<sub>OH</sub>| = I<sub>OL</sub> = 6 mA (min)
- Balanced propagation delays: t<sub>p</sub>LH ≃ t<sub>p</sub>HL
- Pin and function compatible with 74LS646

Note 1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

Note 2: All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

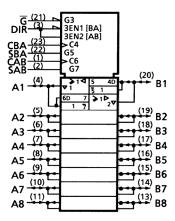
#### **Pin Assignment**



2007-10-01



### **IEC Logic Symbol**



#### **Truth Table**

G	DIR	CAB	СВА	SAB	SBA	А	В	Function	
		Х	Х	X	Х	Inputs	Inputs	The output functions of A and B busses are	
Н	X	(Note)	(Note)	^		Z	Z	disabled.	
	^	$\bot$		X	Х	Х	Х	Both A and B busses are used as inputs to the internal flip-flops. Data on the bus will be stored on the rising edge of the clock.	
		Х	X			Inputs	Outputs		
		(Note)	(Note)	L	Х	L	L	The data on the A bus are displayed on the B bus.	
		(Note)	(Note)			Н	Н		
	н		Х	L	х	L	L	The data on the A bus are displayed on the B bus,	
L			(Note)			Н	Н	and are stored into the A storage flip-flops on the rising edge of CAB.	
		Х	Х	Х	х	Х	Qn	The data in the A storage flip-flops are displayed	
		<u> </u>	(Note)	п				on the B bus.	
			Х	Н	х	L	L	The data on the A bus are stored into the A	
			(Note)	п		Н	Н	storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B bus.	
		X (Note)  X L (Note)			L	Outputs	Inputs		
				Х		L	L	The data on the B bus are displayed on the A bus.	
			(Note)			Н	Н		
					L	L	L	The data on the B bus are displayed on the A bus,	
L	L			Х		Н	Н	and are stored into the B storage flip-flops on the rising edge of CBA.	
		X (Note)	Х	· ·		Qn	Х	The data in the B storage flip-flops are displayed	
			(Note)	Х	Н			on the A bus.	
		Х				L	L	The data on the B bus are stored into the B	
		(Note)		Х	Н	Н	Н	storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A bus.	

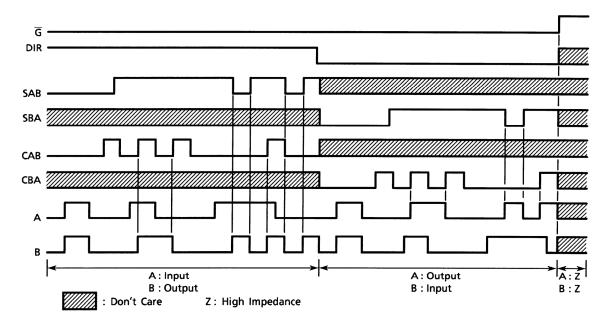
X: Don't care

Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

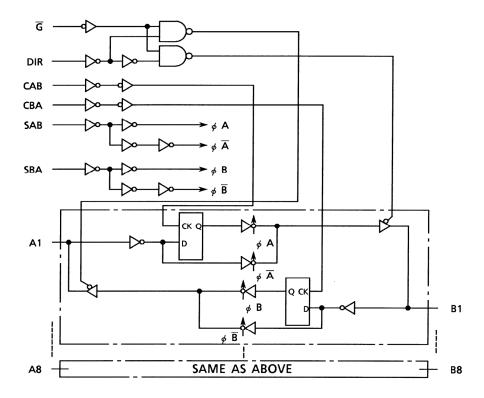
Z: High impedance

Note: The clock are not internally gated with either  $\overline{\mathsf{G}}$  or DIR. Therefore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

# **Timing Chart**



### **System Diagram**



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#### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit	
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V	
DC input voltage	V <sub>IN</sub>	-0.5~V <sub>CC</sub> + 0.5	V	
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V	
Input diode current	I <sub>IK</sub>	±20	mA	
Output diode current	lok	±20	mA	
DC output current	lout	±35	mA	
DC V <sub>CC</sub> /ground current	I <sub>CC</sub>	±75	mA	
Power dissipation	P <sub>D</sub>	500 (DIP) (Note 2)	mW	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

#### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5~5.5	V
Input voltage	V <sub>IN</sub>	0~V <sub>CC</sub>	٧
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0~500	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition V <sub>CC</sub> (V)		-	Га = 25°C		Ta = -4	Unit		
Characteristics	Symbol			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
High-level input voltage	V <sub>IH</sub>	_		4.5~5.5	2.0	_	_	2.0		V
Low-level input voltage	V <sub>IL</sub>	_		4.5~5.5	_	_	0.8	_	0.8	V
High-level output	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	V
voltage			I <sub>OH</sub> = -6 mA	4.5	4.18	4.31	_	4.13	_	
Low-level output	V <sub>OL</sub>	VIN = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	V
voltage			I <sub>OL</sub> = 6 mA	4.5		0.17	0.26	_	0.33	V
3-state output off state current	I <sub>OZ</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND		5.5			±0.5	_	±5.0	μΑ
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply	Icc	$V_{IN} = V_{CC}$ or	r GND	5.5			4.0	_	40.0	μΑ
current	Ic	Per input: V <sub>IN</sub> = 0.5 V or 2.4 V Other input: V <sub>CC</sub> or GND		5.5	_	_	2.0	_	2.9	mA

# Timing Requirements (input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	Ta =	25°C	Ta = -40 ~85°C	Unit		
			V <sub>CC</sub> (V)	Тур.	Limit	Limit		
Minimum pulse width	imum pulse width t <sub>W (L)</sub>		4.5	_	15	19		
(CK)	tw (H)	_	5.5	_	14	17	ns	
Minimum set-up time			4.5	_	10	13	ns	
Millimum set-up time	ts	_	5.5	—	9	12		
Minimum hold time	4.		4.5	_	5	5	20	
Willimum noid time	t <sub>h</sub>	_	5.5	_	5	5	ns	
Clock fraguency	f		4.5	_	31	25	MHz	
Clock frequency	'	_	5.5	_	37	30	IVIHZ	



# AC Characteristics (input: $t_r = t_f = 6$ ns)

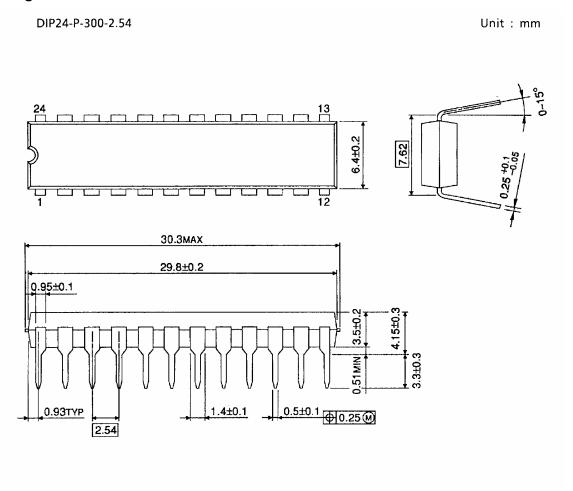
Characteristics	Symbol	Test Co	ondition		Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol		CL (pF)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	01.110
Output transition time	t <sub>TLH</sub>		50	4.5	_	7	12	_	15	ns
Output transition time	t <sub>THL</sub>	_	50	5.5	_	6	11	_	14	
			50	4.5	_	20	30	_	38	
Propagation delay time	$t_{pLH}$	_		5.5	_	17	27	_	34	ns
(BUS-bus)	$t_{pHL}$		150	4.5	_	25	38	_	48	110
			100	5.5	_	22	34	_	43	
Decree of the delay			50	4.5	_	29	44	_	55	
Propagation delay time	$t_{pLH}$			5.5	_	26	40	_	50	ns
(CAB, CBA-bus)	$t_{pHL}$		150	4.5	_	34	52	_	65	
			100	5.5	_	31	47	_	59	
Decree the delect	t <sub>pLH</sub>	_	50	4.5	_	24	34	_	43	ns
Propagation delay time				5.5	_	21	31	_	39	
(SAB, SBA-bus)	t <sub>pHL</sub>		150	4.5	_	29	42	_	53	
				5.5	_	26	38	_	46	
			50	4.5	_	26	38	_	48	ns
Output enable time	$t_{pZL}$	$R_{I} = 1 k\Omega$		5.5	_	23	34	_	43	
(DIR, G-bus)	$t_{pZH}$		150	4.5	_	31	46	_	58	
			100	5.5	_	28	41	_	52	
Output disable time	$t_{pLZ}$	$R_L = 1 \text{ k}\Omega$	50	4.5	_	26	35	_	44	ns
(DIR, G-bus)	$t_{pHZ}$	TAL - TRUE		5.5	_	23	32	_	40	110
Maximum clock	f <sub>max</sub>		50	4.5	31	55	_	25	_	MHz
frequency	·IIIax			5.5	37	61	_	30	_	1411.12
Input capacitance	C <sub>IN</sub>	DIR, $\overline{G}$ , SAB, SBA, CAB, CBA		_	5	10	_	10	pF	
Output capacitance	C <sub>I/O</sub>	An, Bn			_	13	_	_	_	pF
Power dissipation	$C_{PD}$	_	_		_	40			_	pF
capacitance	(Note)					70				Pi

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC}$  (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per bit)

# **Package Dimensions**



Weight: 1.50 g (typ.)

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